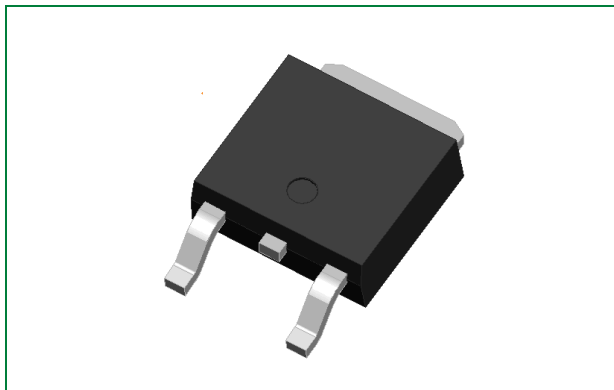


LGD18N45TH 450 V, 18 A N-Channel Ignition IGBT

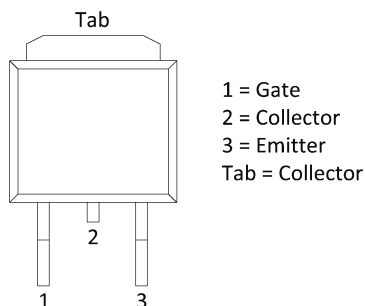


Agency Approvals

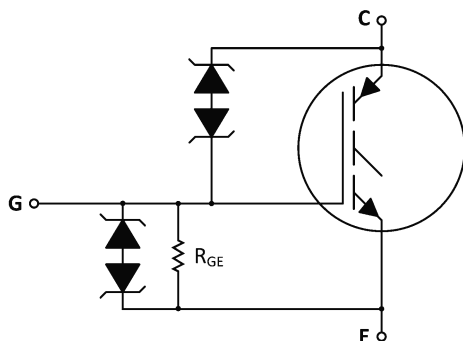
Environmental Approvals



Pinout Diagram



Functional Diagram



Product Summary

Characteristic	Value	Unit
V_{CES}	450	V
I_c	18	A

Description

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Over-Voltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

Features

- Ideal for Coil-on-Plug Applications
- DPAK Package Offers Smaller Footprint for Increased Board Space
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Low Threshold Voltage Interfaces Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- AEC-Q101 Qualified
- These are Pb-Free Devices
- Emitter Ballasting for Short-Circuit Capability

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1. Maximum Ratings (T_J = 25 °C unless otherwise specified)

Characteristic	Conditions	Symbol	Value	Unit
Collector-Emitter Voltage	-	V _{CES}	500	V _{DC}
Gate-Gate Voltage	-	V _{CER}	500	V _{DC}
Gate-Emitter Voltage	-	V _{GE}	18	V _{DC}
Collector Current – Continuous	T _C = 25 °C	I _C	18	A _{DC}
Collector Current – Pulsed			50	A _{AC}
ESD – Human Body Model	R = 1500 Ω, C = 100 pF	ESD	8.0	kV
ESD – Machine Model	R = 0 Ω, C = 200 pF		400	V
Total Power Dissipation	T _C = 25 °C	P _D	115	W
	Derating for > 25 °C		0.77	W/°C
Operating and Storage Temperature Range	-	T _J , T _{stg}	-55 to +175	°C

2. Unclamped Collector-to-Emitter Avalanche Characteristics

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy			
V _{CC} = 50 V, V _{GE} = 5.0 V, P _{kL} = 26.0 A, L = 1.0 mH, Starting T _J = 25 °C	E _{AS}	338	mJ
V _{CC} = 50 V, V _{GE} = 5.0 V, P _{kL} = 10.0 A, L = 8.4 mH, Starting T _J = 25 °C		420	
V _{CC} = 50 V, V _{GE} = 5.0 V, P _{kL} = 15.4 A, L = 2.0 mH, Starting T _J = 150 °C		237	
V _{CC} = 50 V, V _{GE} = 5.0 V, P _{kL} = 5.7 A, L = 15.2 mH, Starting T _J = 150 °C		247	

3. Maximum Short-Circuit Times

Characteristic	Symbol	Value	Unit
Short Circuit Withstand Time 1 (T _A = 105 °C) ¹	t _{sc,1-1}	1000	μs
Short Circuit Withstand Time 1 (T _A = 150 °C) ¹	t _{sc,1-2}	800	μs
Short Circuit Withstand Time 2 (T _A = 105 °C) ²	t _{sc,2-1}	5.0	ms
Short Circuit Withstand Time 2 (T _A = 150 °C) ²	t _{sc,2-2}	1.0	ms

Footnote 1: See Figure 17, 3 pulses with 10 ms period

Footnote 2: See Figure 18, 3 pulses with 10 ms period

4. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.3	°C/W
Thermal Resistance, Junction to Ambient (DPAK) ³	R _{θJA}	95	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T _L	275	°C

Footnote 3: When surface mounted to an FR4 board using the minimum recommended pad size

5. Electrical Characteristics – Off

Characteristic	Symbol	Conditions	Temperature	Value			Unit
				Min	Typ	Max	
Collector-Emitter Clamp Voltage	BV_{CES}	$I_C = 2.0 \text{ mA}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	430	455	470	V_{DC}
		$I_C = 10 \text{ mA}$		440	475	500	
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 15 \text{ V}, V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$	-	-	2.0	μA_{DC}
			$T_J = 25^\circ\text{C}$	-	0.5	20	
		$V_{CE} = 350 \text{ V}, V_{GE} = 0 \text{ V}$	$T_J = 150^\circ\text{C}$	-	75	250	
			$T_J = -40^\circ\text{C}$	-	0.2	10	
Reverse Collector-Emitter Leakage Current	I_{ECS}	$V_{CE} = -24 \text{ V}$	$T_J = 25^\circ\text{C}$	-	0.7	1.0	mA
			$T_J = 150^\circ\text{C}$	-	12	25	
			$T_J = -40^\circ\text{C}$	-	0.1	1.0	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75 \text{ mA}$	$T_J = 25^\circ\text{C}$	24	27	30	V_{DC}
			$T_J = 150^\circ\text{C}$	26	29	33	
			$T_J = -40^\circ\text{C}$	23	26	29	
Gate-Emitter Clamp Voltage	BV_{GES}	$I_G = 5.0 \text{ mA}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	11	13	15	V_{DC}
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 10 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	384	590	700	μA_{DC}
Gate-Emitter Resistor	R_{GE}	-	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	10	16	26	$k\Omega$
Gate Resistor	R_G	-	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	-	70	-	Ω

6. Electrical Characteristics – On

Characteristic	Symbol	Conditions	Temperature	Value			Unit
				Min	Typ	Max	
Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0 \text{ mA}, V_{GE} = V_{CE}$	$T_J = 25^\circ\text{C}$	1.1	1.56	1.9	V_{DC}
			$T_J = 150^\circ\text{C}$	0.75	1.08	1.4	
			$T_J = -40^\circ\text{C}$	1.2	1.75	2.1	
Threshold Temperature Coefficient (Negative)	-	-	-	-	3.5	-	$mV/^\circ\text{C}$
Collector-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 7.0 \text{ A}, V_{GE} = 4.5 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	1.10	1.84	2.30	V_{DC}
		$I_C = 7.0 \text{ A}, V_{GE} = 4.0 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	1.15	1.89	2.35	
		$I_C = 7.0 \text{ A}, V_{GE} = 3.7 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	1.20	1.93	2.50	
		$I_C = 10 \text{ A}, V_{GE} = 4.5 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	1.45	2.07	2.65	
		$I_C = 10 \text{ A}, V_{GE} = 4.0 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	1.50	2.13	2.80	
		$I_C = 10 \text{ A}, V_{GE} = 3.7 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	1.55	2.19	2.85	
		$I_C = 10 \text{ mA}, V_{GE} = 4.5 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	-	0.65	1.00	
Forward Transconductance	g_{fs}	$V_{CS} = 5.0 \text{ V}, I_C = 6.0 \text{ A}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	6.0	14	25	Mhos

7. Dynamic Characteristics

Characteristic	Symbol	Conditions	Temperature	Value			Unit
				Min	Typ	Max	
Input Capacitance	C_{ISS}	$V_{CC} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1.0 \text{ MHz}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	400	780	1000	pF
Output Capacitance	C_{OSS}			50	72	100	
Transfer Capacitance	C_{RSS}			4	6	10	

8. Switching Characteristics

Characteristic	Symbol	Conditions	Temperature	Value			Unit
				Min	Typ	Max	
Turn-off Delay Time	$t_{d(off)}$	$V_{CC} = 300\text{ V}$, $V_{GE} = 0\text{ V}$, $R_G = 1.0\text{ k}\Omega$, $R_L = 46\text{ }\Omega$	$T_J = 25\text{ }^\circ\text{C}$	1.0	2.9	12	μs
Fall Time	t_f	$V_{CC} = 300\text{ V}$, $V_{GE} = 5\text{ V}$, $R_G = 1.0\text{ k}\Omega$, $R_L = 46\text{ }\Omega$		1.0	2.5	7.0	
Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 14\text{ V}$, $V_{GE} = 5\text{ V}$, $R_G = 1.0\text{ k}\Omega$, $R_L = 1\text{ }\Omega$	$T_J = 25\text{ }^\circ\text{C}$	0.1	0.42	1.4	μs
Rise Time	t_r	$V_{CC} = 14\text{ V}$, $V_{GE} = 5\text{ V}$, $R_G = 1.0\text{ k}\Omega$, $R_L = 1\text{ }\Omega$		1.0	2.5	9.0	

9. Figure Data

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

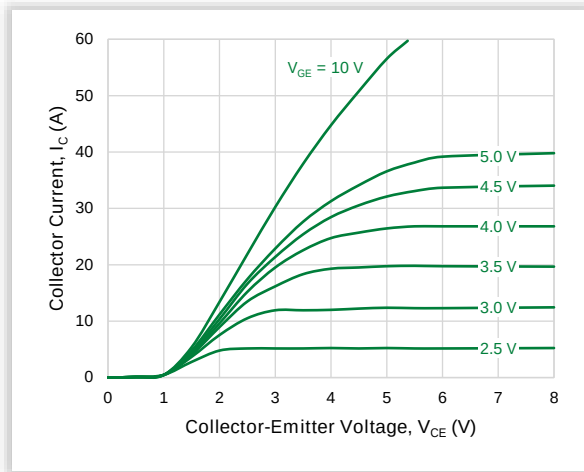


Figure 2. Output Characteristics ($T_J = -40^\circ\text{C}$)

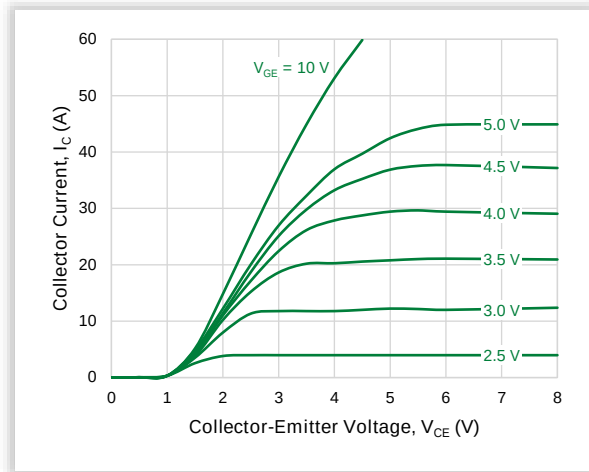


Figure 3. Output Characteristics ($T_J = 150^\circ\text{C}$)

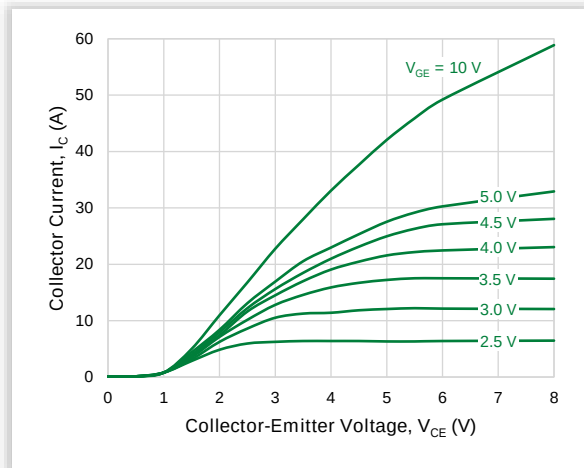


Figure 4. Transfer Characteristics

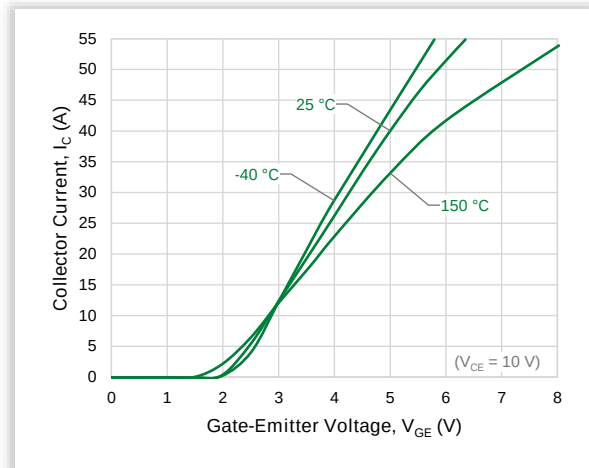


Figure 5. Collector-Emitter Saturation Voltage vs. Junction Temperature

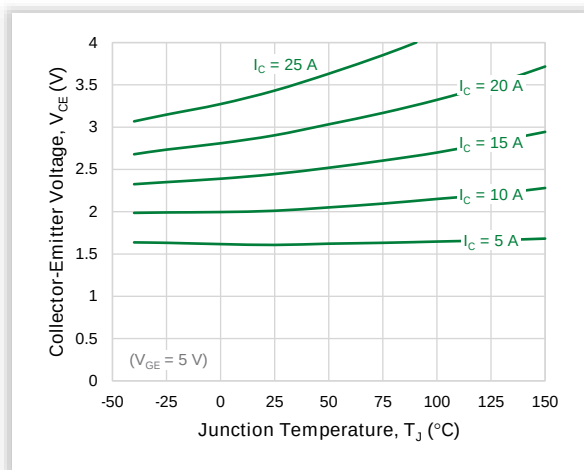


Figure 6. Collector-Emitter Voltage vs. Gate-Emitter Voltage ($T_J = 25^\circ\text{C}$)

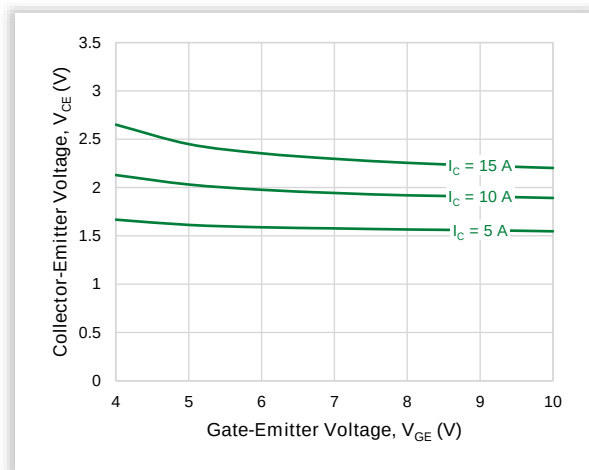


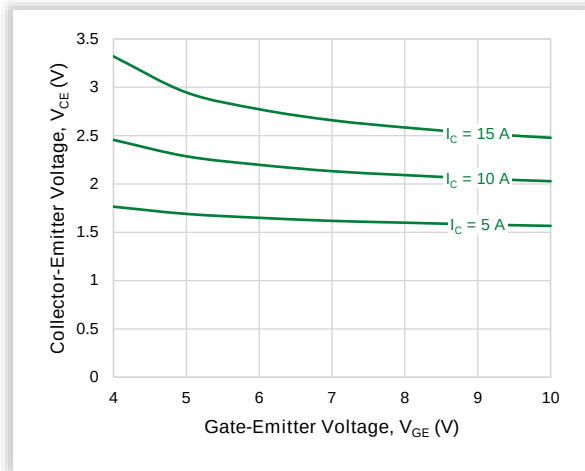
Figure 7. Collector-Emitter Voltage vs. Gate-Emitter Voltage ($T_J = 150^\circ\text{C}$)


Figure 8. Capacitance Variation

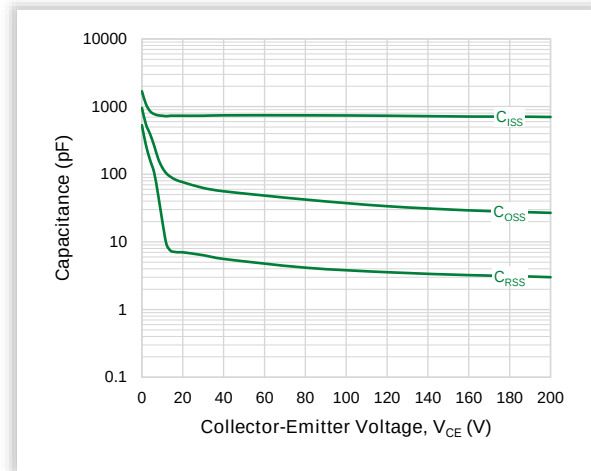


Figure 9. Gate Threshold Voltage vs. Temperature

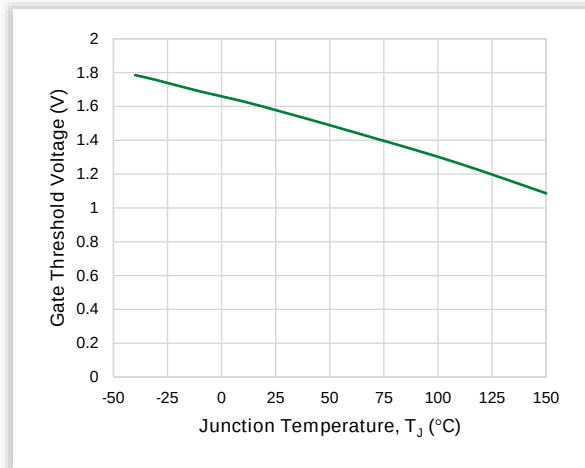


Figure 10. Minimum Open Secondary Latch Current vs. Inductance

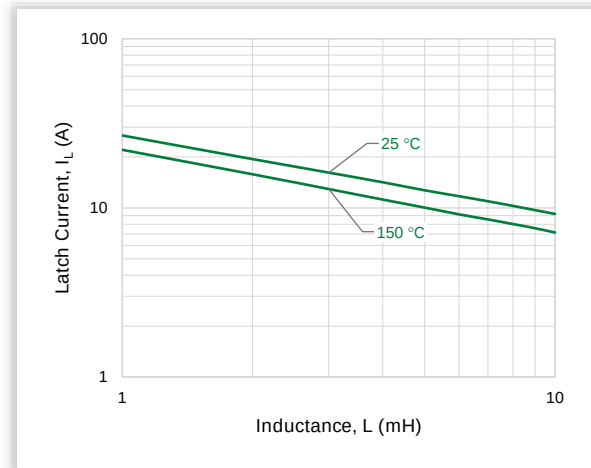


Figure 11. Typical Open Secondary Latch Current vs. Inductance

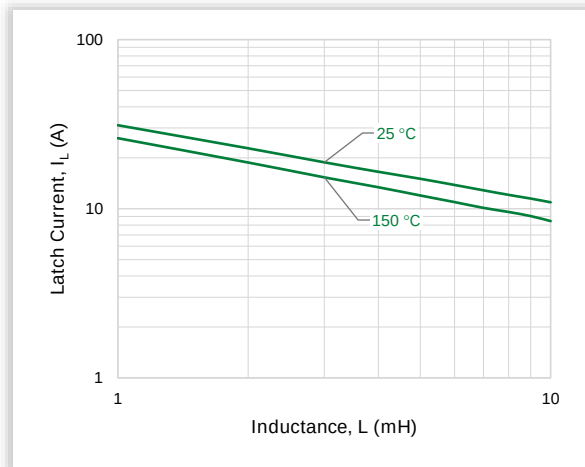


Figure 12. Inductive Switching Fall Time vs. Temperature

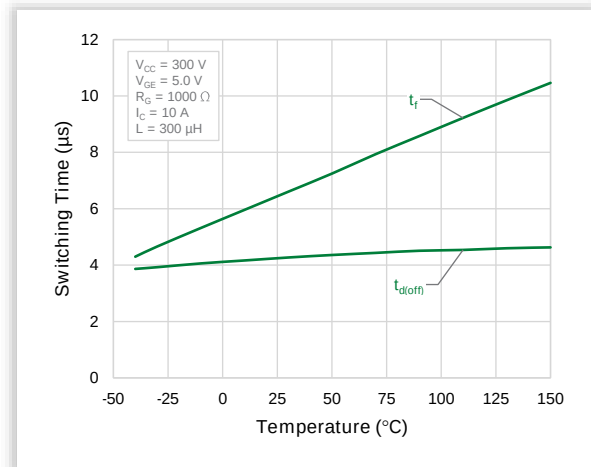


Figure 13. Single Pulse Safe Operating Area

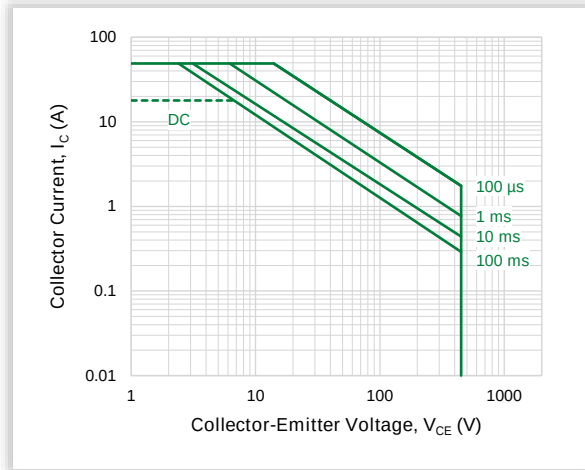
 (Mounted on an Infinite Heatsink at $T_A = 25^\circ\text{C}$)


Figure 14. Single Pulse Safe Operating Area

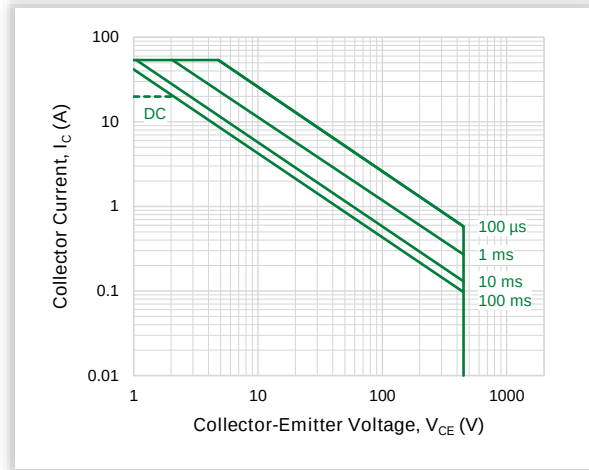
 (Mounted on an Infinite Heatsink at $T_A = 125^\circ\text{C}$)


Figure 15. Pulse Train Safe Operating Area

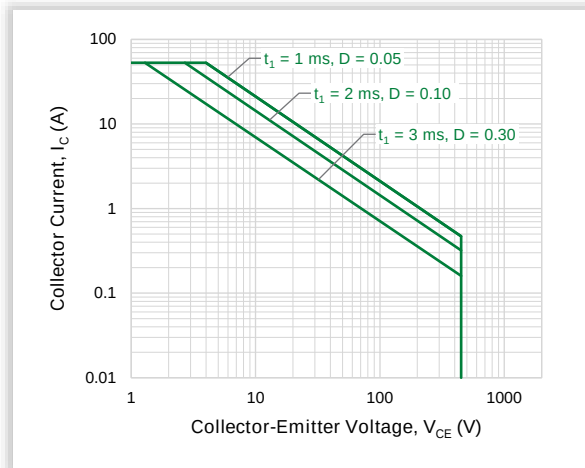
 (Mounted on an Infinite Heatsink at $T_A = 25^\circ\text{C}$)


Figure 16. Pulse Train Safe Operating Area

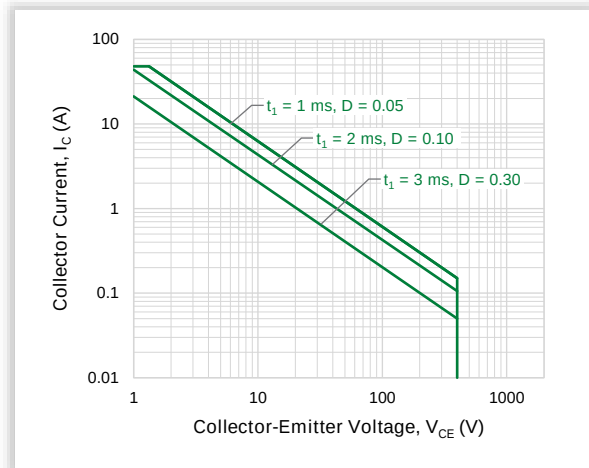
 (Mounted on an Infinite Heatsink at $T_A = 125^\circ\text{C}$)


Figure 17. Circuit Configuration for Short Circuit Test 1

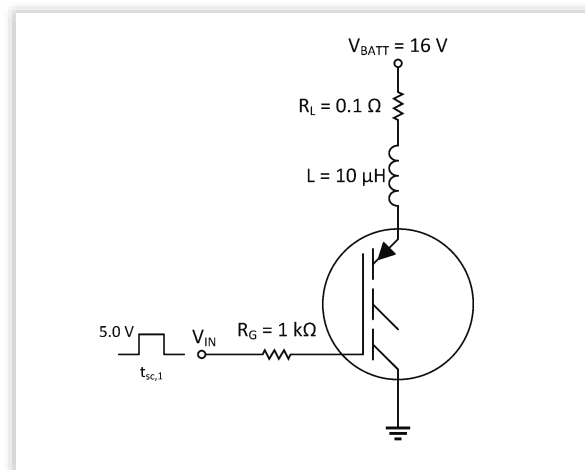


Figure 18. Circuit Configuration for Short Circuit Test 2

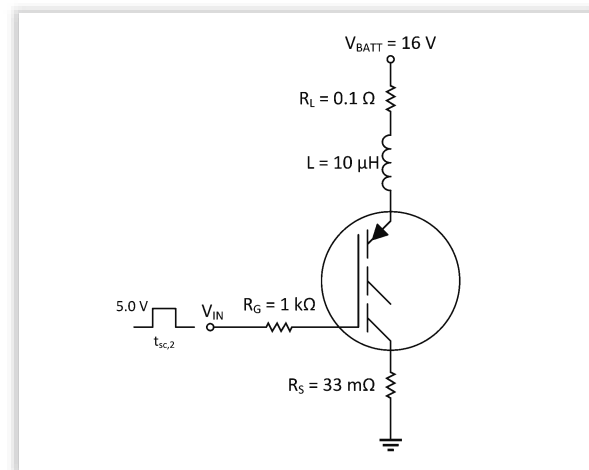
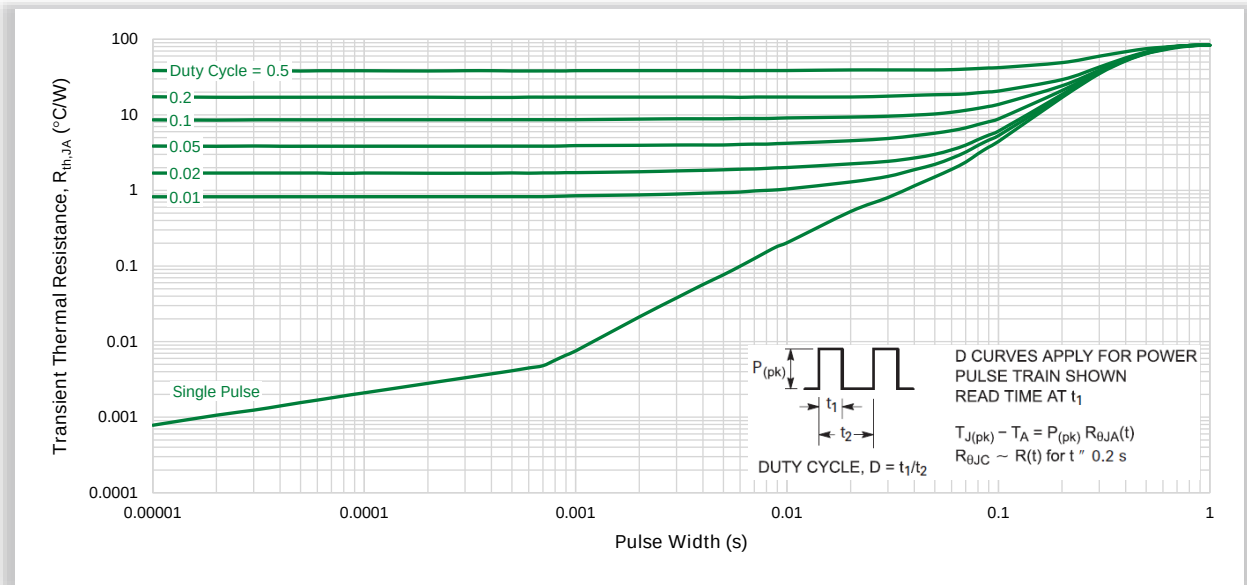
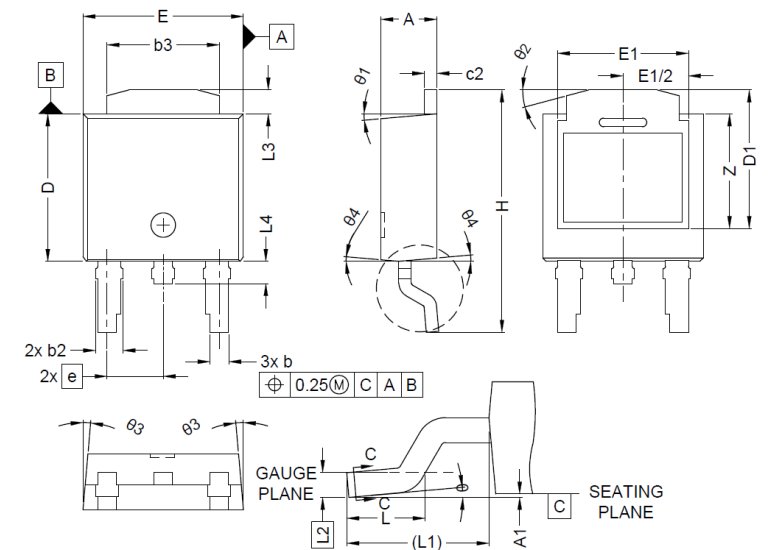


Figure 19. Transient Thermal Resistance

(Non-normalized Junction-Ambient mounted on minimum pad area)



10. Package Dimensions



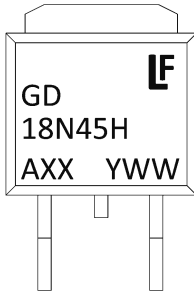
Recommended Solder Pad Layout:

Notes:

1. DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
3. HEAT SINK SIDE FLASH IS MAX. 0.8mm.
4. RADIUS ON TERMINAL IS OPTIONAL.

Symbol	Millimeters		
	Min	Nom	Max
A	2.18	-	2.38
A1	0.00	-	0.13
b	0.63	-	0.89
b2	0.72	-	1.14
b3	4.57	-	5.46
c	0.46	-	0.61
c2	0.46	-	0.61
D	5.97	-	6.22
D1	5.45	-	5.85
E	6.35	-	6.73
E1	5.14	-	5.54
e	2.29 BSC		
H	9.40	-	10.41
L	1.40	-	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	-	1.27
L4	-	-	1.01
Z	3.93	-	-
theta	0°	-	10°
theta1	0°	-	10°
theta2	10°	-	20°
theta3	0°	-	10°
theta4	0°	-	10°

11. Part Numbering and Marking



GD18N45H = Device Code
 A = Assembly Location
 XX = Lot Number
 Y = Year
 WW = Work Week
 H = Ballast Structure Design

12. Packing Options

Part Number	Package	Packing Mode	M.O.Q.
LGD18N45TH	DPAK (Pb-Free)	Tape & Reel	2500

For additional information please visit www.Littelfuse.com/powersemi

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